

[MEMORY DEVICE STRUCTURE AND METHOD FOR MANUFACTURING THE SAME]

Abstract of Disclosure

File: 9112USF.RTF12The present invention provides a memory structure, comprising: a substrate; a gate oxide layer disposed on a portion of the substrate; a gate structure disposed on the gate oxide layer; a buried bit line disposed in the substrate along both sides of the gate structures; a raised line disposed on the buried bit line; an isolating spacer disposed on both sidewalls of the gate structure and a word line disposed over the substrate in a direction perpendicular to the buried bit line; and an insulation layer disposed on a top of the raised line to electrically isolate the raised line and the word line.

Figures